



Advanced High Voltage Isolated Gate Driver with Segmented Drive for SiC MOSFETs

GD3160

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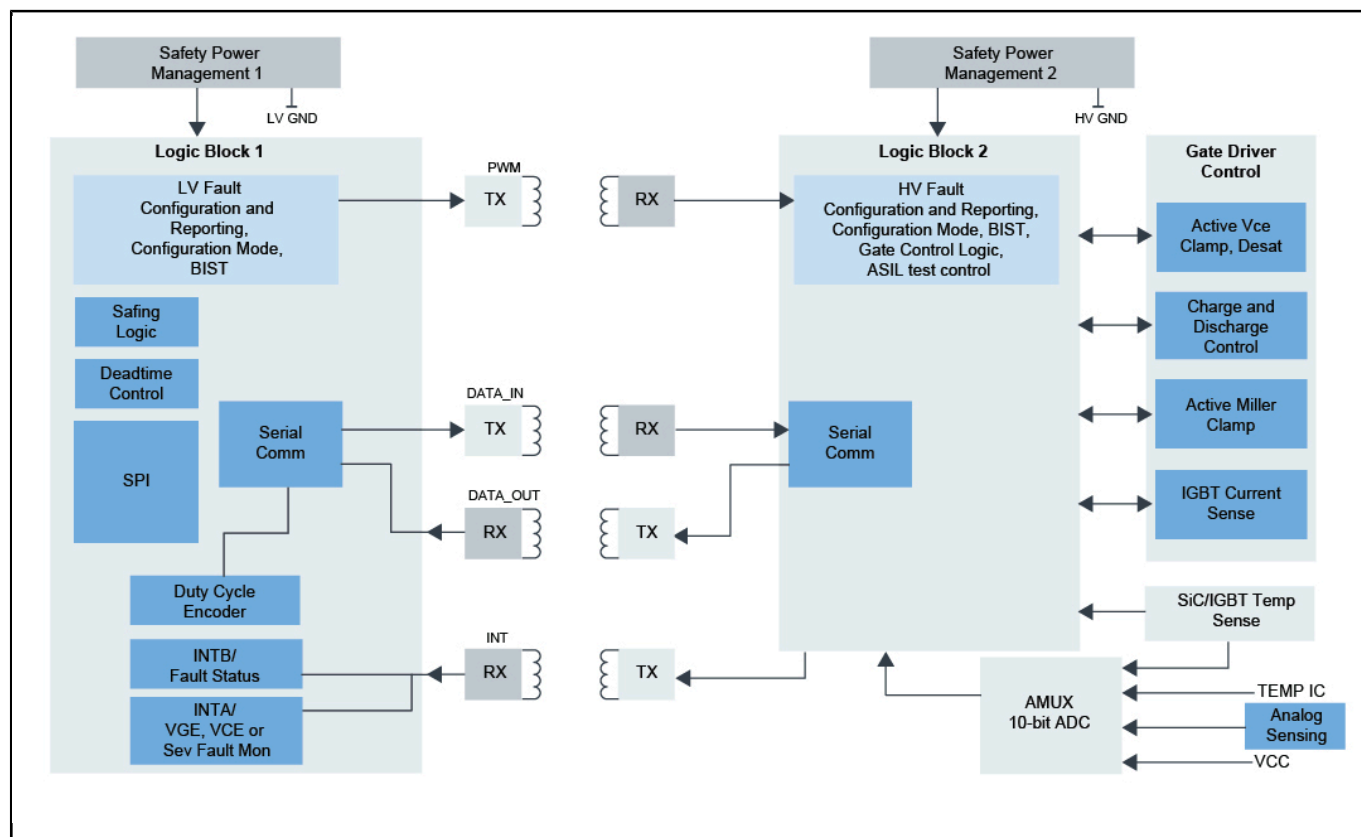
GD3160 silicon and enablement (documentation, software and boards) are available for selected customers (NDA required). For additional information and sample availability [contact support](#) or your local sales representative.

The GD3160 is an improved, advanced single-channel high-voltage isolated gate driver with enhanced features for driving and protecting silicon carbide (SiC) MOSFETs and functional safety.

The GD3160's SPI programmable drive, protection and fault reporting features allow users to optimize conditions for driving and protecting almost any SiC MOSFET or Si IGBT power switch.

ISO 26262 compliant and automotive qualified, the GD3160 integrates BOM saving and functional safety features to support implementing ASIL D compliant and power density efficient xEV inverter solutions.

Advanced High Voltage Isolated GD with Segmented Drive for SiC MOSFETs Block Diagram



View additional information for [Advanced High Voltage Isolated Gate Driver with Segmented Drive for SiC MOSFETs](#).

Note: The information on this document is subject to change without notice.

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